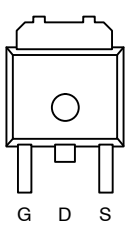


N-Channel 20-V (D-S) 175°C MOSFET

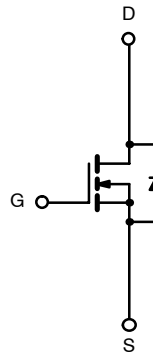
PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
20	0.011 @ $V_{GS} = 10$ V	18
	0.020 @ $V_{GS} = 4.5$ V	13.5

TO-252


Top View

Drain Connected to Tab



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature
- PWM Optimized for High Efficiency
- 100% R_g Tested

APPLICATIONS

- High-Side Synchronous Buck DC/DC Conversion
 - Desktop
 - Server

Ordering Information: SUD50N02-11P
SUD50N02-11P—E3 (Lead Free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current ^a	I_D	$T_A = 25^\circ\text{C}$	18	A
		$T_C = 100^\circ\text{C}$	13	
Pulsed Drain Current	I_{DM}	100		
Continuous Source Current (Diode Conduction) ^a	I_S	4.1		
Maximum Power Dissipation	P_D	$T_A = 25^\circ\text{C}$	6.25	W
		$T_C = 25^\circ\text{C}$	38 ^a	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	19	$^\circ\text{C}/\text{W}$
		Steady State	40	
Maximum Junction-to-Case	R_{thJC}	3.2	3.9	

Notes

- Surface Mounted on FR4 Board, $t \leq 10$ sec.
- Limited by package

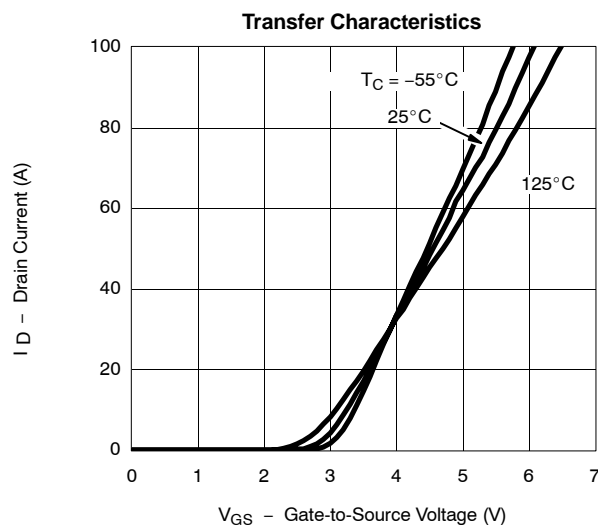
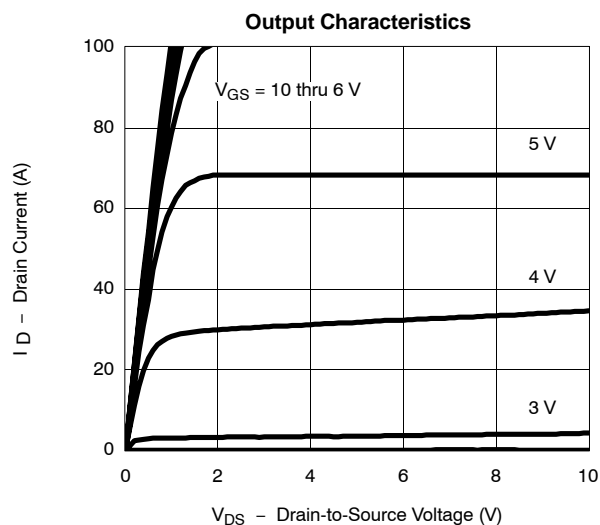
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ ^a	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.8		3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 125 °C			50	
On-State Drain Current ^b	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	50			A
Drain-Source On-State Resistance ^b	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		0.0086	0.011	Ω
		V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C			0.0165	
		V _{GS} = 4.5 V, I _D = 20 A		0.016	0.020	
Forward Transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 20 A	15			S
Dynamic^a						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 10 V, f = 1 MHz		1190		pF
Output Capacitance	C _{oss}			435		
Reverse Transfer Capacitance	C _{rss}			190		
Gate Resistance	R _g		1.7	3.5	5.5	Ω
Total Gate Charge ^c	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 50 A		9.2	14	nC
Gate-Source Charge ^c	Q _{gs}			4		
Gate-Drain Charge ^c	Q _{gd}			3		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 10 V, R _L = 0.2 Ω I _D ≅ 50 A, V _{GEN} = 10 V, R _g = 2.5 Ω		11	20	ns
Rise Time ^c	t _r			10	15	
Turn-Off Delay Time ^c	t _{d(off)}			30	45	
Fall Time ^c	t _f			9	15	
Source-Drain Diode Ratings and Characteristic (T_C = 25 °C)						
Pulsed Current	I _{SM}				100	A
Diode Forward Voltage ^b	V _{SD}	I _F = 50 A, V _{GS} = 0 V		1.2	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		25	50	ns

Notes

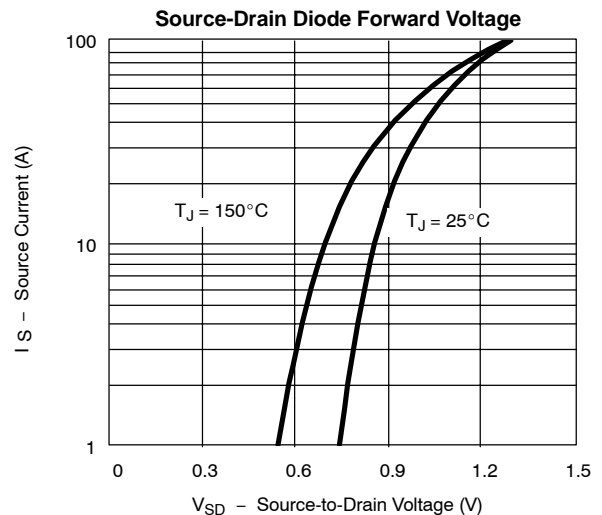
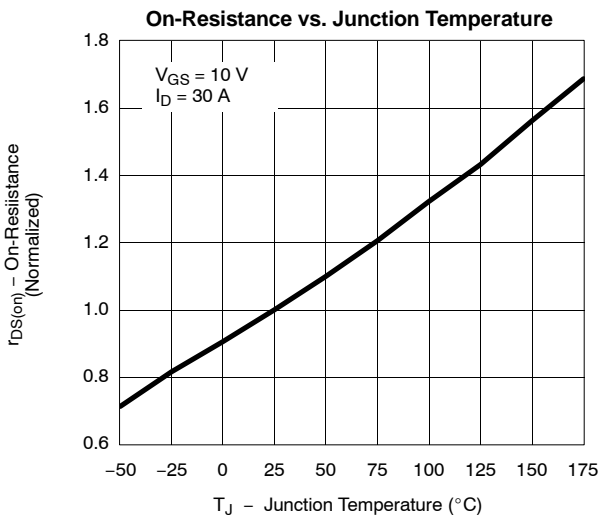
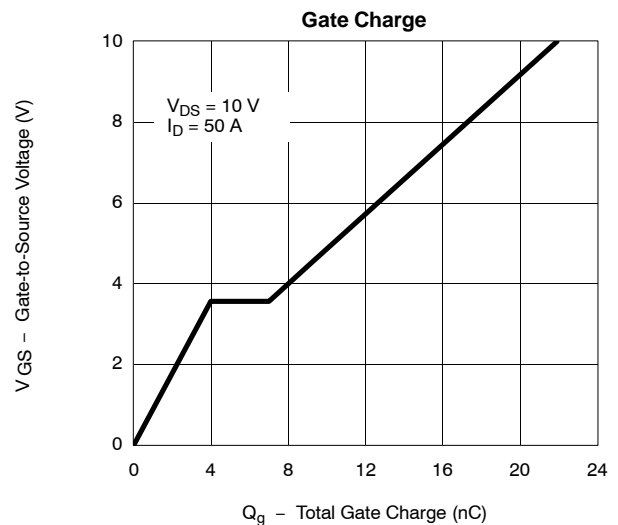
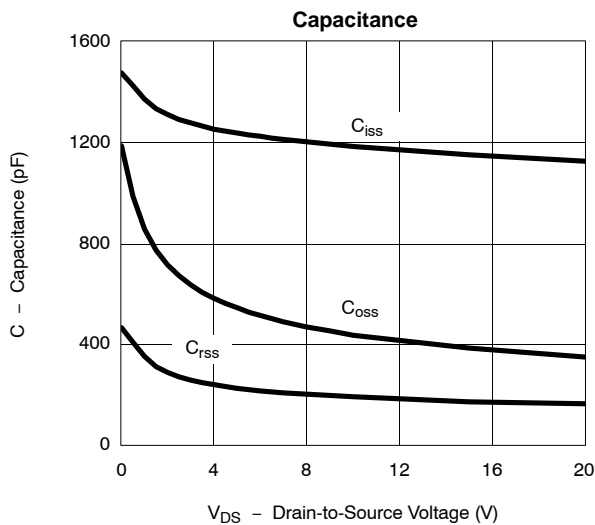
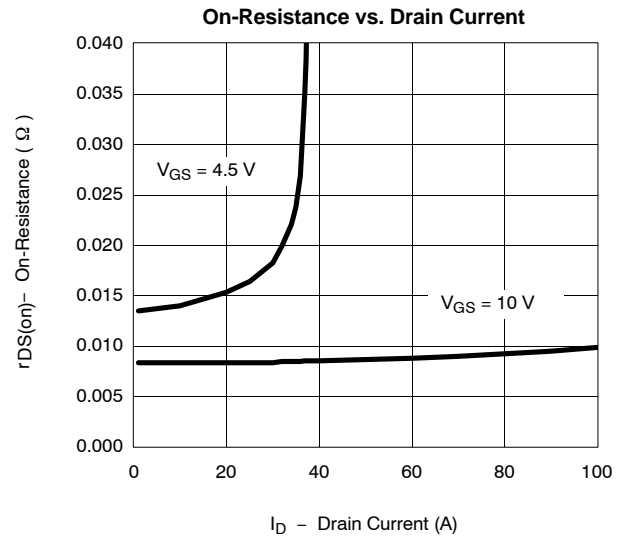
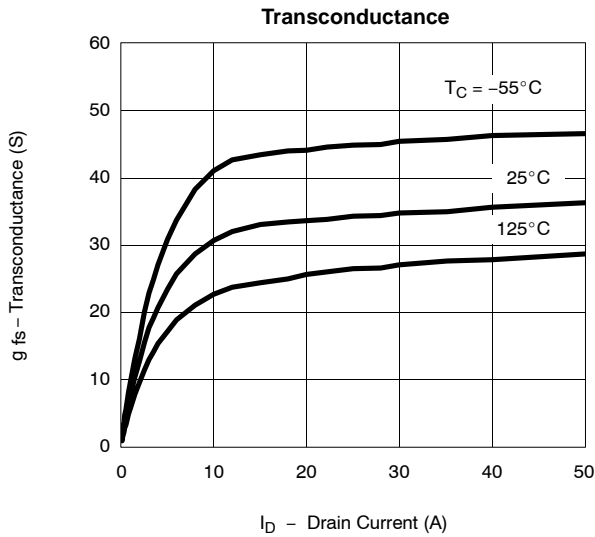
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





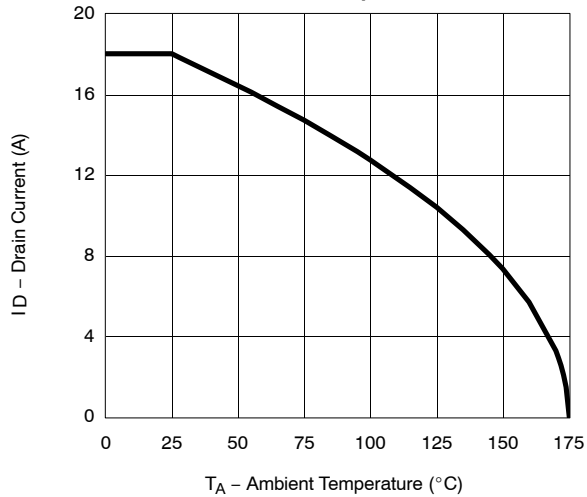
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



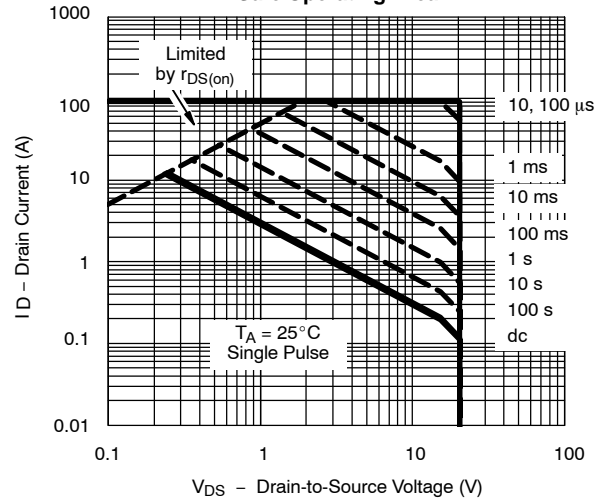


THERMAL RATINGS

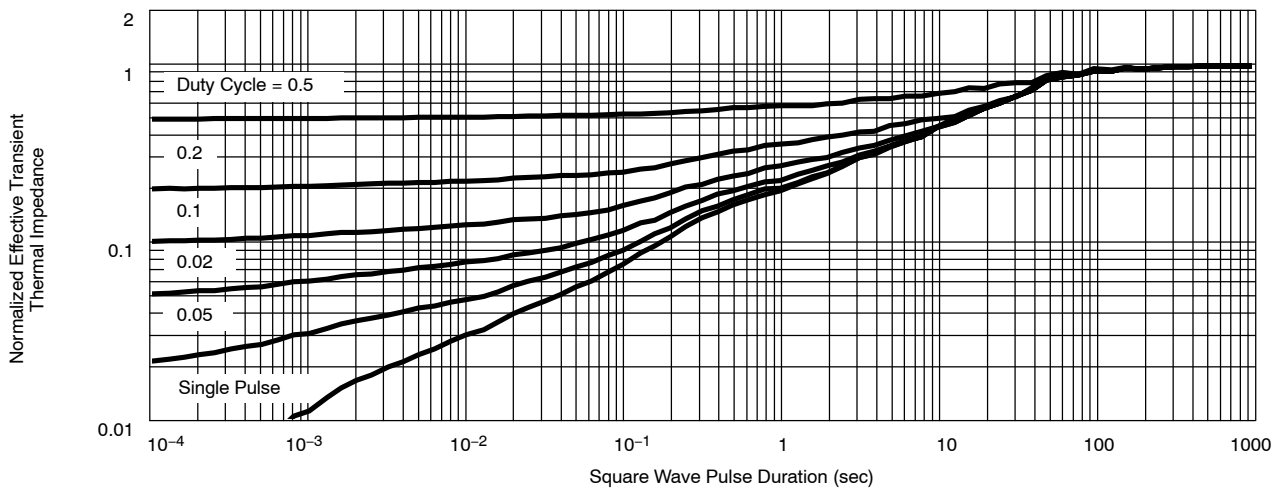
Maximum Drain Current vs. Ambient Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.